

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	1	nvcpd near sensor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 13:43
S2	1	nvcpd	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/07 11:15
S3	2	scan\$4 same wafer same sensor same voltage same vibrat\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/07 11:16
S4	85	scan\$4 same wafer same sensor same voltage	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/07 11:22
S5	57	vibrat\$3 with contact with potential with difference	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/07 11:22
S6	21	vibrat\$3 with contact with potential with difference and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/07 13:20
S7	5	non near vibrat\$3 with contact with potential with difference	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/07 13:04
S8	6	non near vibrat\$3 with potential with difference	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/07 13:05
S9	1	vibrat\$3 with contact with potential with difference and semiconductor and defect and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/07 13:08
S10	2	vibrat\$3 with contact with potential with difference and semiconductor and defect	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/07 13:09
S11	12	vibrat\$3 with contact with potential with difference and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/19 11:07
S12	1	1991-213740.NRAN.	DERWENT	OR	OFF	2004/09/07 13:20

S13	7	defect same semiconductor and contact same potential same difference same sensor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/13 12:42
S14	7	defect same semiconductor and contact same potential same difference same vibrat\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/13 12:45
S15	0	defect same semiconductor and Kelvin same (non near vibrat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/13 12:46
S16	11	defect same semiconductor and Kelvin same vibrat\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/13 12:46
S17	4	category with defect with chemical	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/19 10:59
S18	9	category with defect with electronic	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/19 10:53
S19	71	treat with defect with improv\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/19 11:00
S20	6	treat with defect with improv\$3 and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/19 11:01
S21	99	treat\$3 with defect with improv\$3 and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/19 11:02
S22	329	treat\$5 with defect with improv\$3 and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/19 11:02
S23	6	(analyz\$3 analysis) with chemical with contaminant with auger	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/19 11:08
S24	119	take.inv. and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/09/23 12:23

S25	1	wafer near handler and remed\$4 with defect and clean\$3 and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 12:30
S26	1	wafer near handler and remed\$4 with defect and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 12:30
S27	39	wafer near handler and clean\$3 with defect and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 12:32
S28	25	wafer near handler and clean\$3 with defect and semiconductor and sensors!	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 12:35
S29	27	wafer near handler and clean\$3 same defect and semiconductor and sensors!	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 14:41
S30	518	sensors! same clean\$3 same (semiconductor wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 14:42
S31	36	sensors! same clean\$3 same (semiconductor wafer) same handl\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 14:43
S32	13	438/906.ccls. and sensors!	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 15:11
S33	26	438/906.ccls. and sensors	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 15:12
S34	9	438/12.ccls. and sensors	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 15:12
S35	6	438/12.ccls. and sensors!	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 15:14
S36	18	438/12.ccls. and clean\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 15:20

S37	6	438/12.ccls. and sensors!	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 15:21
S38	3	sensors! same clean\$3 same semiconductor same defect	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 15:23
S39	14	sensors same clean\$3 same semiconductor same defect	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 16:03
S40	0	sensors same remed\$4 same semiconductor same defect	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 16:02
S41	96	sensors same clean\$3 same semiconductor and defect	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 16:03
S42	3	sensors same clean\$3 same semiconductor same monitor\$3 and defect	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 16:05
S43	64	134/1.3.ccls. and sensors!	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 16:16
S44	24	134/1.2.ccls. and sensors!	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 16:16
S45	269	transport\$3 same clean same (semiconductor wafer) same handl\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/24 12:34
S46	0	transport\$3 same clean same (semiconductor wafer) same handl\$3 same defect	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/24 12:34
S47	71	transport\$3 same clean same (semiconductor wafer) same handl\$3 and defect	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/24 12:36
S48	0	transport\$3 same clean\$4 same (semiconductor wafer) same handl\$3 same defect	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/24 12:37

S49	111	transport\$3 same clean\$4 same (semiconductor wafer) same handl\$3 and defect	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/24 12:50
S50	46	transport\$3 same defect same (semiconductor wafer) same handl\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/24 13:02
S51	31	monitor\$3 with clean\$3 same (semiconductor wafer) same sensors!	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/24 13:17
S52	7	determin\$3 same cleanliness same wafer same improv\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/24 13:20
S53	7	determin\$3 same cleanliness same semiconductor same improv\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/24 13:21
S54	594	modify\$3 same clean\$3 same improv\$	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/24 13:21
S55	36	modify\$3 same clean\$3 same improv\$ same (wafer semiconductor)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/24 13:22
S56	28	decompos\$3 with signal with wavelet with domain	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 13:43
S57	6	decompos\$3 with signal with wavelet with domain and coefficient and peak	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 13:52
S58	118	signal with wavelet with domain and coefficient and peak	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 13:52
S59	87	signal with wavelet with domain and coefficient and peak and \$2compos\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 14:42
S60	6	\$2compos\$3 with signal with wavelet with domain and coefficient and peak	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 13:52

S61	32	signal with wavelet with domain and coefficient and peak and \$2compos\$3 and revers\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 13:53
S62	13	signal with wavelet with domain and coefficient and peak and revers\$3 near order	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 13:57
S63	30	signal with wavelet with domain and coefficient and peak and revers\$3 and \$2compress\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 14:48
S64	8	signal with wavelet with domain and coefficient and peak and revers\$3 same coefficient and \$2compress\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 14:11
S65	0	model with circuit with RC and convert\$3 with discrete with time and impulse near response and deconvolut\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 14:13
S66	1	model with circuit and convert\$3 with discrete with time and impulse near response and deconvolut\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 14:21
S67	4	model\$3 with circuit and convert\$3 with discrete with time and impulse near response and deconvolut\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 14:23
S68	14	non near vibrat\$4 with contact with potential with difference with sensor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 14:26
S69	8	non near vibrat\$4 with contact with potential with difference with sensor and defect\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 14:26
S70	5	signal with wavelet with domain and coefficient and peak and backward and \$2compress\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 14:50
S71	28	signal with wavelet with domain and coefficient and peak and (transpos\$3 invert\$3) and \$2compress\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 15:01
S72	0	signal with wavelet with domain and coefficient and peak and (transpos\$3 invert\$3) same coefficient and \$2compress\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 14:50

S73	8	signal with wavelet with domain and coefficient and peak and (revers\$3) same coefficient and \$2compress\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 15:02
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